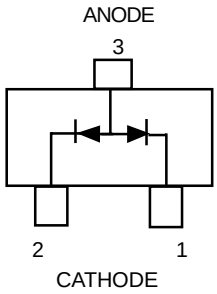
Common Anode Silicon Dual Switching diodes

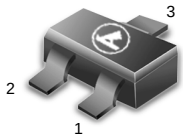
M1MA151WAT1
M1MA152WAT1

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC-59 package which is designed for low power surface mount applications.

- Fast t_{rr}, < 10 ns
- Low C_D, < 15 pF
- Available in 8 mm Tape and Reel
  Use M1MA151/2WAT1 to order the 7 inch/3000 unit reel.
  Use M1MA151/2WAT3 to order the 13 inch/10,000 unit reel.

SC-59 PACKAGE
COMMON ANODE
DUAL SWITCHING DIODES
40/80 V-100mA
SURFACE MOUNT





CASE 318D–03, STYLE5
SC–59

MAXIMUM RATINGS (T_A = 25°C)

Rating		Symbol	Value	Unit
Reverse Voltage	M1MA151WAT1	V_R	40	Vdc
	M1MA152WAT1		80	
Peak Reverse Voltage	M1MA151WAT1	V_{RM}	40	Vdc
	M1MA152WAT1		80	
Forward Current	Single	I_F	100	mAdc
	Dual		150	
Peak Forward Current	Single	I_{FM}	225	mAdc
	Dual		340	
Peak Forward Surge Current	Single	I_{FSM} (1)	500	mAdc
	Dual		750	

THERMAL CHARACTERISTICS

Rating	Symbo	IMax	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

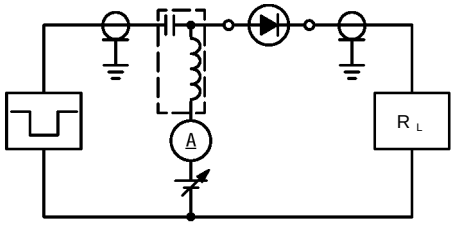
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	M1MA151WAT1	I_R	V_R = 35 V	—	0.1	μAdc
	M1MA152WAT1		V_R = 75 V	—	0.1	
Forward Voltage		V_F	I_F = 100 mA	—	1.2	Vdc
Reverse Breakdown Voltage	M1MA151WAT1	V_R	I_R = 100 μA	40	—	Vdc
	M1MA152WAT1			80	—	
Diode Capacitance		C_D	V_R = 0, f = 1.0 MHz	—	15	pF
Reverse Recovery Time		t_{rr} (2)	I_F = 10 mA, V_R = 6.0 V, R_L = 100Ω, I_{rr} = 0.1 I_R	—	10	ns

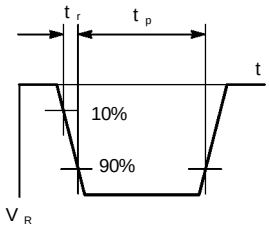
1. t = 1 SEC
2. t_{rr} Test Circuit

M1MA151WAT1 M1MA152WAT1

RECOVERY TIME EQUIVALENT TEST CIRCUIT

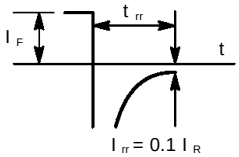


INPUT PULSE



t_p = 2 µs
t_r = 0.35 ns

OUTPUT PULSE

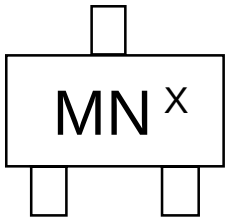


I_F = 10 mA
V_R = 6 V
R_L = 100 Ω

DEVICE MARKING—EXAMPLE

Marking Symbol

Type No.	151WA	152WA
Symbol	MN	MO



The “X” represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.